

RoHS Compliant and Pb-Free Product
Package Style: Flanged Ceramic

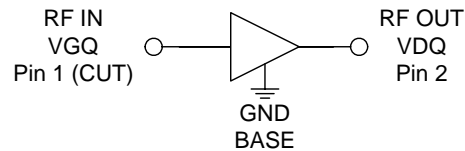


Features

- Peak Power=120W
- Gain=14dB
- Advanced GaN HEMT Technology
- 48V Operation
- Optimized Evaluation Board Layout for 50Ω Operation

Applications

- Commercial Wireless Infrastructure
- Cellular and WiMAX Infrastructure
- General Purpose Broadband Amplifiers
- Public Mobile Radios
- Industrial, Scientific and Medical



Functional Block Diagram

Product Description

The RF3934 is designed for commercial infrastructure, cellular and WiMAX infrastructure and general purpose broadband amplifier applications. Using an advanced high power density Gallium Nitride (GaN) semiconductor process, these high-performance amplifiers achieve high efficiency and flat gain over a broad frequency range in a single amplifier design. The RF3934 is an unmatched GaN transistor packaged in a flanged ceramic package which provides excellent thermal stability through the use of advanced heat sink and power dissipation technologies. Ease of integration is accomplished through the incorporation of simple, optimized matching networks external to the package that provide wideband gain and power performance in a single amplifier.

Ordering Information

RF3934

GaN Wide-Band Power Amplifier

Optimum Technology Matching® Applied

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|--------------------------------------|--------------------------------------|-------------------------------------|--|
| <input type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input checked="" type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | |

RF3934

Proposed

RFMD 

rfmd.com

**Please contact
RFMD Technical Support
at (336) 678-5570
for more information.**